

Amend the application identified above as follows:

IN THE CLAIMS

Amend claims 29 and 30 as follows:

~~29. (Once Amended) A method of co-planarizing copper or copper-based metallurgy and a refractory metal-based barrier layer or liner in an interlevel dielectric layer of a semiconductor device comprising the steps of:~~

~~planarizing said copper or copper-based metallurgy using a first slurry comprising an oxidizing agent consisting of a metal-based compound, an oxidation inhibitor, a surfactant and an abrasive comprising alumina in water; said first slurry having a pH of between 1.2 and 2.5 and said first slurry for removing copper selectively with respect to said barrier layer or liner;~~

~~co-planarizing said barrier layer or liner and said interlevel dielectric layer using a second slurry comprising a peroxide agent, an oxidation inhibitor, a surfactant and an abrasive comprising silica in water; said second slurry having a pH of between 3.0 and 7.5 and said second slurry for removing said barrier layer or liner at a first removal rate and copper at a second removal rate, wherein the first removal rate is greater than the second removal rate.~~

30. (Once Amended) The method of claim 29 wherein said surfactant in both the first and second slurries comprises a sulfated fatty acid.

Add the following new claims:

31. The method of claim 29, wherein said metal-based compound comprises ferric nitrate.

32. The method of claim 29, wherein the first removal rate is about eight times greater than the second removal rate.

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